

Narendra Kumar

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

19
papers

238
citations

10
h-index

15
g-index

22
ext. papers

316
ext. citations

5.3
avg, IF

3.35
L-index

#	Paper	IF	Citations
19	Rapid, Multianalyte Detection of Opioid Metabolites in Wastewater.. <i>ACS Nano</i> , 2022 ,	16.7	5
18	Phase-Controllable Synthesis of Ultrathin Molybdenum Nitride Crystals Via Atomic Substitution of MoS ₂ . <i>Chemistry of Materials</i> , 2022 , 34, 351-357	9.6	3
17	Interface mechanisms involved in a-IGZO based dual gate ISFET pH sensor using Al ₂ O ₃ as the top gate dielectric. <i>Materials Science in Semiconductor Processing</i> , 2020 , 119, 105239	4.3	7
16	Dielectrophoresis assisted rapid, selective and single cell detection of antibiotic resistant bacteria with G-FETs. <i>Biosensors and Bioelectronics</i> , 2020 , 156, 112123	11.8	27
15	Modulation Doping via a Two-Dimensional Atomic Crystalline Acceptor. <i>Nano Letters</i> , 2020 , 20, 8446-8452.	12.5	16
14	A cleanroom in a glovebox. <i>Review of Scientific Instruments</i> , 2020 , 91, 073909	1.7	4
13	Detection of a multi-disease biomarker in saliva with graphene field effect transistors. <i>Medical Devices & Sensors</i> , 2020 , 3, e10121	1.6	4
12	Stacked Top Gate Dielectrics in Dual Gate Ion Sensitive Field Effect Transistors: Role of Interfaces. <i>ACS Applied Electronic Materials</i> , 2019 , 1, 1465-1473	4	8
11	Evidence for Helical Hinge Zero Modes in an Fe-Based Superconductor. <i>Nano Letters</i> , 2019 , 19, 4890-4896.	11.5	29
10	Role of deposition and annealing of the top gate dielectric in a-IGZO TFT-based dual-gate ion-sensitive field-effect transistors. <i>Semiconductor Science and Technology</i> , 2017 , 32, 035013	1.8	13
9	Investigation of Mechanisms Involved in the Enhanced Label Free Detection of Prostate Cancer Biomarkers Using Field Effect Devices. <i>Journal of the Electrochemical Society</i> , 2017 , 164, B409-B416	3.9	11
8	Signal Amplification in Field Effect-Based Sandwich Enzyme-Linked Immunosensing by Tuned Buffer Concentration with Ionic Strength Adjuster. <i>Applied Biochemistry and Biotechnology</i> , 2016 , 179, 168-78	3.2	2
7	Back-Channel Electrolyte-Gated a-IGZO Dual-Gate Thin-Film Transistor for Enhancement of pH Sensitivity Over Nernst Limit. <i>IEEE Electron Device Letters</i> , 2016 , 37, 500-503	4.4	41
6	Enhanced pH sensitivity over the Nernst limit of electrolyte gated a-IGZO thin film transistor using branched polyethylenimine. <i>RSC Advances</i> , 2016 , 6, 10810-10815	3.7	20
5	Functionalized vertically aligned ZnO nanorods for application in electrolyte-insulator-semiconductor based pH sensors and label-free immuno-sensors. <i>Journal of Physics: Conference Series</i> , 2016 , 704, 012013	0.3	8
4	Sensitivity Enhancement Mechanisms in Textured Dielectric based Electrolyte-Insulator-Semiconductor (EIS) Sensors. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, N18-N23	2	10
3	Low temperature annealed amorphous indium gallium zinc oxide (a-IGZO) as a pH sensitive layer for applications in field effect based sensors. <i>AIP Advances</i> , 2015 , 5, 067123	1.5	12

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| 2 | Effect of post deposition annealing temperature of e-beam evaporated Ta ₂ O ₅ films on sensitivities of electrolyte-insulator-semiconductor devices 2015 , | 6 |
| 1 | Sensitivity Enhancement of Electrolyte/Insulator/Semiconductor Sensors Using Mesotextured and Nanotextured Dielectric Surfaces. <i>IEEE Sensors Journal</i> , 2015 , 15, 2039-2045 | 4 12 |